

N-CHANNEL POWER MOSFET

BSS123LT1

FEATURE

- **Pb-Free package is available**
RoHS product for packing code suffix "G"
Halogen free product for packing code suffix "H"

DEVICE MARKING AND ORDERING INFORMATION

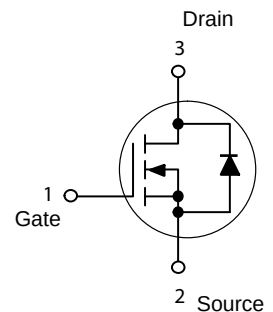
Device	Marking	Shipping
BSS123LT1	SA	3000/Tape&Reel



SOT-23

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GSM}	± 40	Vpk
– Non-repetitive ($t_p \leq 50 \mu s$)			
Drain Current	I_D	0.17	Adc
Continuous (Note 1.)	I_{DM}	0.68	
Pulsed (Note 2.)			



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3.)	P_D	225	mW
$T_A = 25^\circ C$		1.8	mW/ $^\circ C$
Derate above $25^\circ C$			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ C$

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.
3. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain–Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 250\ \mu\text{Adc}$)	$V_{(BR)DSS}$	100	–	–	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0$, $V_{DS} = 100\ \text{Vdc}$) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	I_{DSS}	– –	– –	15 60	μAdc
Gate–Body Leakage Current ($V_{GS} = 20\ \text{Vdc}$, $V_{DS} = 0$)	I_{GSS}	–	–	50	nAdc

ON CHARACTERISTICS (Note 4.)

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0\ \text{mAdc}$)	$V_{GS(th)}$	0.8	–	2.8	Vdc
Static Drain–Source On–Resistance ($V_{GS} = 10\ \text{Vdc}$, $I_D = 100\ \text{mAdc}$)	$r_{DS(on)}$	–	5.0	6.0	Ω
Forward Transconductance ($V_{DS} = 25\ \text{Vdc}$, $I_D = 100\ \text{mAdc}$)	g_{fs}	80	–	–	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 25\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{iss}	–	20	–	pF
Output Capacitance ($V_{DS} = 25\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{oss}	–	9.0	–	pF
Reverse Transfer Capacitance ($V_{DS} = 25\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{rss}	–	4.0	–	pF

SWITCHING CHARACTERISTICS(4)

Turn–On Delay Time	(VCC = 30 Vdc, $I_C = 0.28\ \text{Adc}$, $V_{GS} = 10\ \text{Vdc}$, $R_{GS} = 50\ \Omega$)	$t_{d(on)}$	–	20	–	ns
Turn–Off Delay Time		$t_{d(off)}$	–	40	–	ns

REVERSE DIODE

Diode Forward On–Voltage ($I_D = 0.34\ \text{Adc}$, $V_{GS} = 0\ \text{Vdc}$)	V_{SD}	–	–	1.3	V
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4. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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TYPICAL ELECTRICAL CHARACTERISTICS

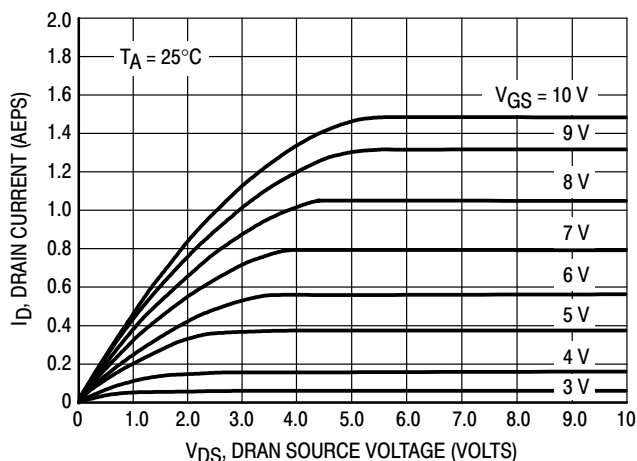


Figure 1. Ohmic Region

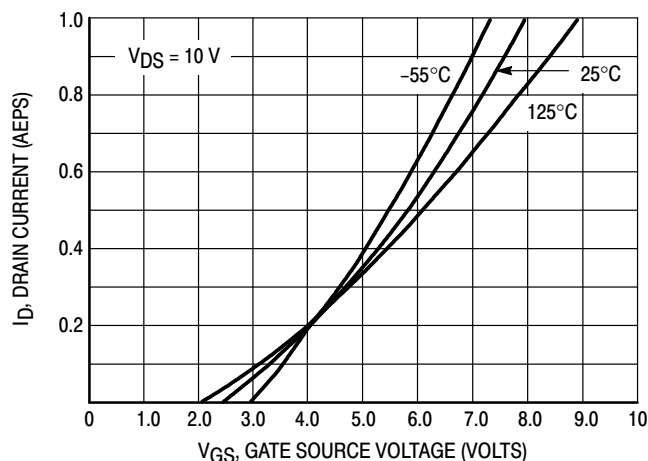


Figure 2. Transfer Characteristics

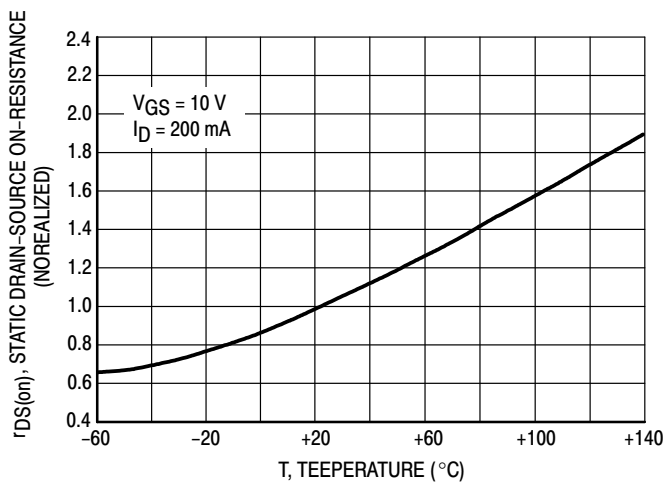


Figure 3. Temperature versus Static Drain-Source On-Resistance

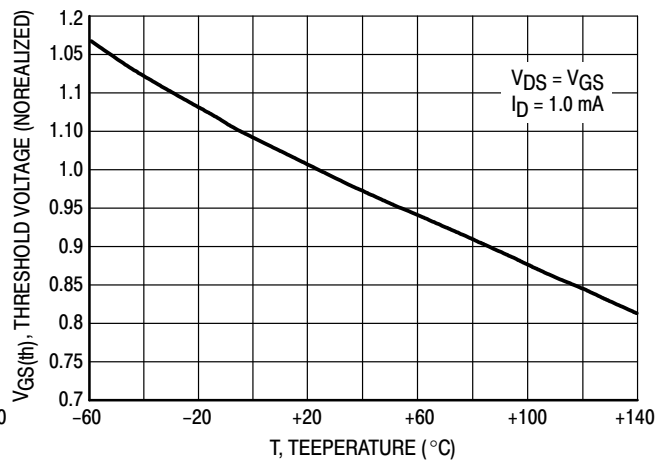
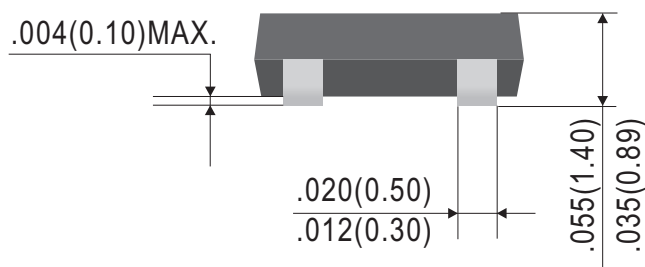
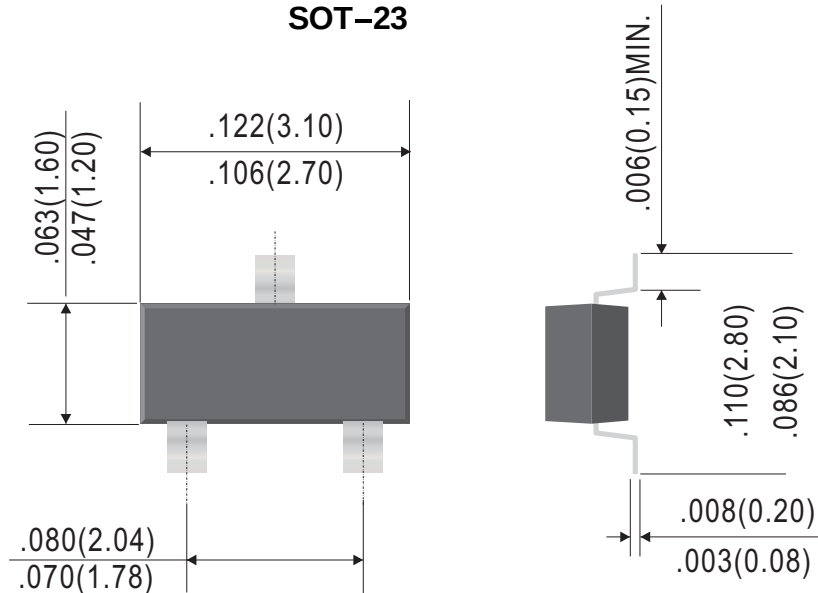


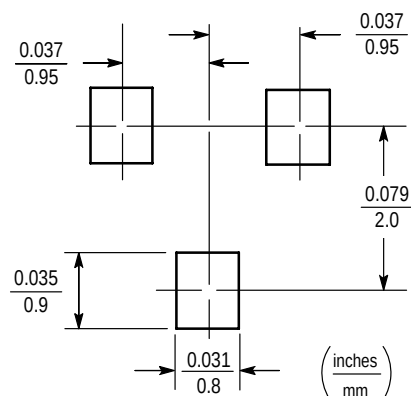
Figure 4. Temperature versus Gate Threshold Voltage

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Dimensions in inches and (millimeters)



N-CHANNEL POWER MOSFET**Ordering Information:**

Device PN	Packing
BSS123LT1G ⁽¹⁾ -WS	Tape&Reel: 3 Kpcs/Reel

Note: (1) RoHS product for packing code suffix "G" ; Halogen free product for packing code suffix "H"

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